

IRHLG7S7214 (2N7614M1)

PD-97832D

Radiation Hardened Logic Level Power MOSFET Thru-Hole (MO-036AB) 250V,0.8A, Quad N-channel, R7 Technology

Features

- 5V CMOS and TTL compatible
- Fast switching
- Single event effect (SEE) hardened
- Low total gate charge
- Simple drive requirements
- Light weight
- Hermetically sealed
- ESD rating: Class 1B per MIL-STD-750, Method 1020

Product Summary

- BV_{DSS} : 250V
- I_D : 0.8A
- $R_{DS(on),max}$: 1.1Ω
- $Q_{G,max}$: 15nC

Potential Applications

- DC-DC converter
- Motor drives

Product Validation

Qualified according to MIL-PRF-19500 for space applications

Description

IR HiRel R7 S-Line Logic Level Power MOSFETs provide simple solution to interfacing CMOS and TTL control circuits to power devices in space and other radiation environments. The threshold voltage remains within acceptable operating limits over the full operating temperature and post radiation. This is achieved while maintaining single event gate rupture and single event burnout immunity. The device is ideal when used to interface directly with most logic gates, linear IC's, micro-controllers, and other device types that operate from a 3.3-5V source. It may also be used to increase the output current of a PWM, voltage comparator or an operational amplifier where the logic level drive signal is available.

Ordering Information

Table 1 Ordering options

Part number	Package	Screening Level	TID Level
IRHLG7S7214	MO-036AB	COTS	100 krad(Si)
IRHLG7S7214SCS	MO-036AB	S-Level	100 krad(Si)
IRHLG7S3214	MO-036AB	COTS	300 krad(Si)
IRHLG7S3214SCS	MO-036AB	S-Level	300 krad(Si)



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Absolute Maximum Ratings

1 Absolute Maximum Ratings

Table 2 Absolute Maximum Ratings (Pre-Irradiation)

Symbol	Parameter	Value	Unit
$I_{D1} @ V_{GS} = 4.5V, T_C = 25^{\circ}C$	Continuous Drain Current	0.8	A
$I_{D2} @ V_{GS} = 4.5V, T_C = 100^{\circ}C$	Continuous Drain Current	0.5	A
$I_{DM} @ T_C = 25^{\circ}C$	Pulsed Drain Current ¹	3.2	A
$P_D @ T_C = 25^{\circ}C$	Maximum Power Dissipation	1.4	W
	Linear Derating Factor	0.01	W/ $^{\circ}C$
V_{GS}	Gate-to-Source Voltage	± 10	V
E_{AS}	Single Pulse Avalanche Energy ²	50.4	mJ
I_{AR}	Avalanche Current ¹	0.8	A
E_{AR}	Repetitive Avalanche Energy ¹	0.14	mJ
dv/dt	Peak Diode Reverse Recovery ³	12.3	V/ns
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to +150	$^{\circ}C$
	Lead Temperature	300 (0.063 in. /1.6 mm from case for 10s)	
	Weight	1.3 (Typical)	

¹ Repetitive Rating; Pulse width limited by maximum junction temperature.² $V_{DD} = 50V$, starting $T_J = 25^{\circ}C$, $L = 157mH$, Peak $I_L = 0.8A$, $V_{GS} = 10V$ ³ $I_{SD} \leq 0.8A$, $di/dt \leq 340A/\mu s$, $V_{DD} \leq 250V$, $T_J \leq 150^{\circ}C$

Device Characteristics

2 Device Characteristics

2.1 Electrical Characteristics (Pre-Irradiation)

Table 3 Static and Dynamic Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (Unless Otherwise Specified)

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
BV_{DSS}	Drain-to-Source Breakdown Voltage	250	—	—	V	$V_{GS} = 0V$, $I_D = 250\mu A$
$\Delta BV_{DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.34	—	V/ $^\circ\text{C}$	Reference to 25°C , $I_D = 1.0\text{mA}$
$R_{DS(on)}$	Static Drain-to-Source On-State Resistance	—	—	1.1	Ω	$V_{GS} = 4.5V$, $I_{D2} = 0.5A$ ¹
$V_{GS(th)}$	Gate Threshold Voltage	1.0	—	2.0	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$
$\Delta V_{GS(th)}/\Delta T_J$	Gate Threshold Voltage Coefficient	—	-6.0	—		
G_{fs}	Forward Transconductance	1.0	—	—	S	$V_{DS} = 15V$, $I_{D2} = 0.5A$ ¹
I_{DSS}	Zero Gate Voltage Drain Current	—	—	1.0	μA	$V_{DS} = 200V$, $V_{GS} = 0V$
		—	—	15		$V_{DS} = 200V$, $V_{GS} = 0V$, $T_J = 125^\circ\text{C}$
I_{GSS}	Gate-to-Source Leakage Forward	—	—	100	nA	$V_{GS} = 10V$
	Gate-to-Source Leakage Reverse	—	—	-100		$V_{GS} = -10V$
Q_G	Total Gate Charge	—	—	15	nC	$I_{D1} = 0.8A$
Q_{GS}	Gate-to-Source Charge	—	—	3.5		$V_{DS} = 125V$
Q_{GD}	Gate-to-Drain ('Miller') Charge	—	—	8.3		$V_{GS} = 4.5V$
$t_{d(on)}$	Turn-On Delay Time	—	—	18	ns	$I_{D1} = 0.8A$ ** $V_{DD} = 125V$ $R_G = 7.5\Omega$ $V_{GS} = 5.0V$
t_r	Rise Time	—	—	85		
$t_{d(off)}$	Turn-Off Delay Time	—	—	43		
t_f	Fall Time	—	—	30		
$L_s + L_D$	Total Inductance	—	10	—	nH	Measured from Drain lead (6mm / 0.25 in from package) to Source lead (6mm/ 0.25 in from package) with Source wire internally bonded from Source pin to Drain pin
C_{iss}	Input Capacitance	—	552	—	pF	$V_{GS} = 0V$ $V_{DS} = 25V$ $f = 1.0\text{MHz}$
C_{oss}	Output Capacitance	—	69	—		
C_{rss}	Reverse Transfer Capacitance	—	1.43	—		
R_G	Gate Resistance	—	6.77	—	Ω	$f = 1.0\text{MHz}$, open drain

** Switching speed maximum limits are based on manufacturing test equipment and capability.

¹ Pulse width $\leq 300\mu s$; Duty Cycle $\leq 2\%$

Device Characteristics

2.2 Source-Drain Diode Ratings and Characteristics (Pre-Irradiation)

Table 4 Source-Drain Diode Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
I _S	Continuous Source Current (Body Diode)	—	—	0.8	A	
I _{SM}	Pulsed Source Current (Body Diode) ¹	—	—	3.2	A	
V _{SD}	Diode Forward Voltage	—	—	1.2	V	T _J = 25°C, I _S = 0.8A, V _{GS} = 0V ²
t _{rr}	Reverse Recovery Time	—	—	290	ns	T _J = 25°C, I _F = 0.8A, V _{DD} ≤ 25V di/dt = 100A/μs
Q _{rr}	Reverse Recovery Charge	—	—	388	nC	
t _{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by L _S +L _D)				

2.3 Thermal Characteristics

Table 5 Thermal Resistance

Symbol	Parameter	Min.	Typ.	Max.	Unit
$R_{\theta JC}$	Junction-to-Ambient	—	—	90	$^\circ\text{C}/\text{W}$

2.4 Radiation Characteristics

IR HiRel radiation hardened MOSFETs are tested to verify their radiation hardness capability. The hardness assurance program at IR HiRel is comprised of two radiation environments. Every manufacturing lot is tested for total ionizing dose (per notes 3 and 4) using the TO-3 package. Both pre- and post-irradiation performance are tested and specified using the same drive circuitry and test conditions in order to provide a direct comparison.

2.4.1 Electrical Characteristics — Post Total Dose Irradiation

Table 6 Electrical Characteristics @ $T_J = 25^\circ\text{C}$, Post Total Dose Irradiation ^{3, 4}

Symbol	Parameter	Up to 300 krad (Si) ⁵		Unit	Test Conditions
		Min.	Max.		
BV_{DSS}	Drain-to-Source Breakdown Voltage	250	—	V	$V_{GS} = 0\text{V}$, $I_D = 250\mu\text{A}$
$V_{GS(th)}$	Gate Threshold Voltage	1.0	2.0	V	$V_{DS} = V_{GS}$, $I_D = 250\mu\text{A}$
I_{GSS}	Gate-to-Source Leakage Forward	—	100	nA	$V_{GS} = 10\text{V}$
	Gate-to-Source Leakage Reverse	—	-100		$V_{GS} = -10\text{V}$
I_{DSS}	Zero Gate Voltage Drain Current	—	10	μA	$V_{DS} = 200\text{V}$, $V_{GS} = 0\text{V}$
$R_{DS(on)}$	Static Drain-to-Source On-State Resistance (TO-3) ²	—	0.82	Ω	$V_{GS} = 4.5\text{V}$, $I_{D2} = 0.5\text{A}$
$R_{DS(on)}$	Static Drain-to-Source On-State Resistance (MO-036AB) ²	—	1.1	Ω	$V_{GS} = 4.5\text{V}$, $I_{D2} = 0.5\text{A}$
V_{SD}	Diode Forward Voltage	—	1.2	V	$V_{GS} = 0\text{V}$, $I_F = 0.8\text{A}$

¹ Repetitive Rating; Pulse width limited by maximum junction temperature.

² Pulse width $\leq 300\mu\text{s}$; Duty Cycle $\leq 2\%$

³ Total Dose Irradiation with V_{GS} Bias. $V_{GS} = 10\text{V}$ applied and $V_{DS} = 0$ during irradiation per MIL-STD-750, Method 1019, condition A.

⁴ Total Dose Irradiation with V_{DS} Bias. $V_{DS} = 200\text{V}$ applied and $V_{GS} = 0$ during irradiation per MIL-STD-750, Method 1019, condition A.

⁵ Part numbers IRHLG7S7214 and IRHLG7S3214

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Device Characteristics

2.4.2 Single Event Effects — Safe Operating Area

IR HiRel radiation hardened MOSFETs have been characterized in heavy ion environment for Single Event Effects (SEE). Single Event Effects characterization is illustrated in Fig. 1 and Table 7.

Table 7 Typical Single Event Effects Safe Operating Area

ION	LET (MeV·cm ² /mg)	Energy (MeV)	Range (μm)	V _{DS} (V)			
				V _{GS} = 0V	V _{GS} = -1V	V _{GS} = -5V	V _{GS} = -7V
Kr	35 ± 5%	580 ± 5%	70 ± 5%	250	250	250	250
Xe	60 ± 7.5%	1050 ± 5%	79 ± 5%	250	250	—	—

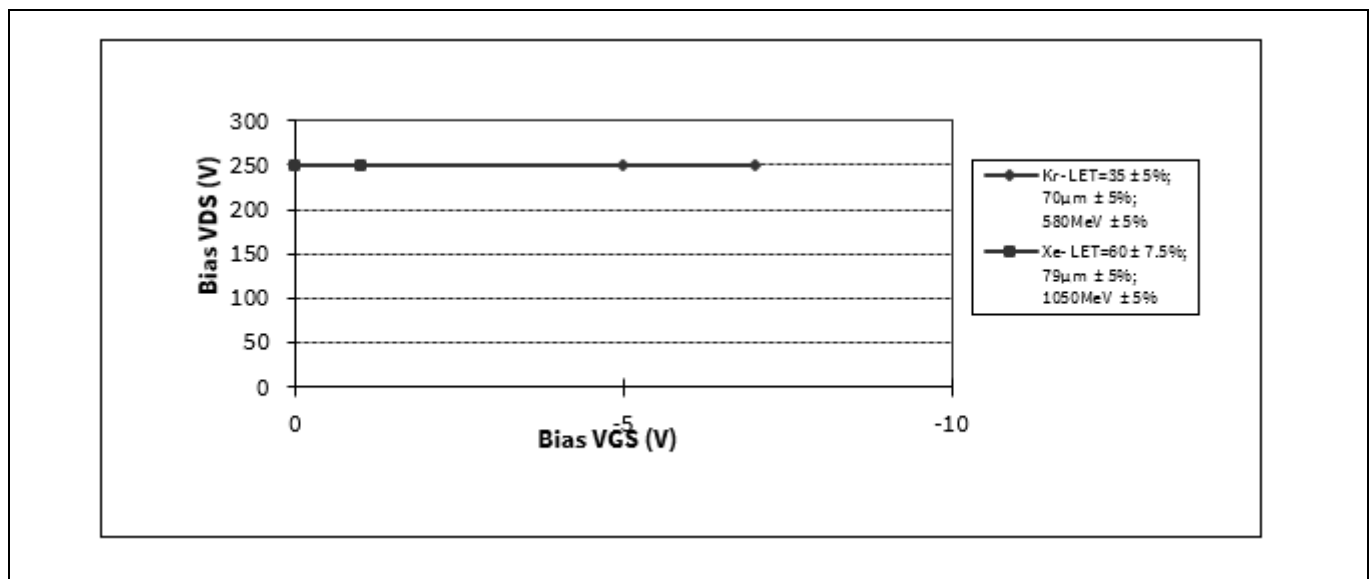


Figure 1 Typical Single Event Effect, Safe Operating Area

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Electrical Characteristics Curves (Pre-irradiation)

3 Electrical Characteristics Curves (Pre-irradiation)

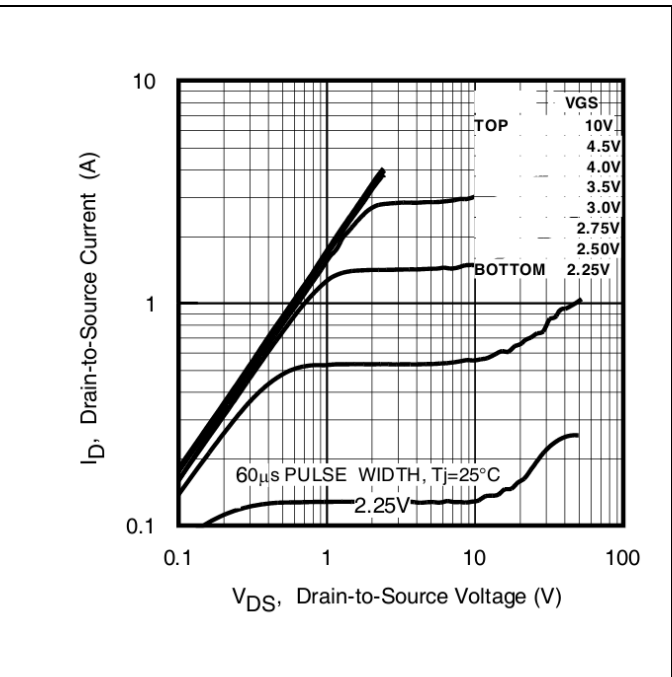


Figure 2 Typical Output Characteristics

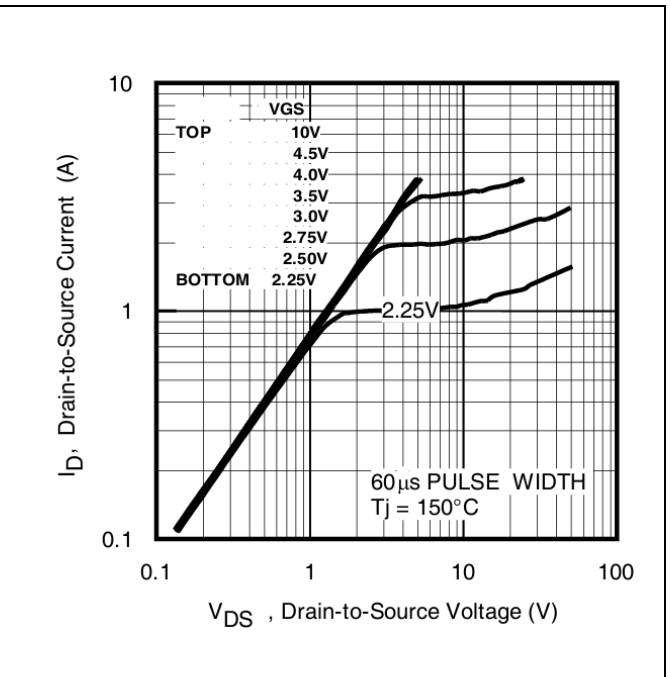


Figure 3 Typical Output Characteristics

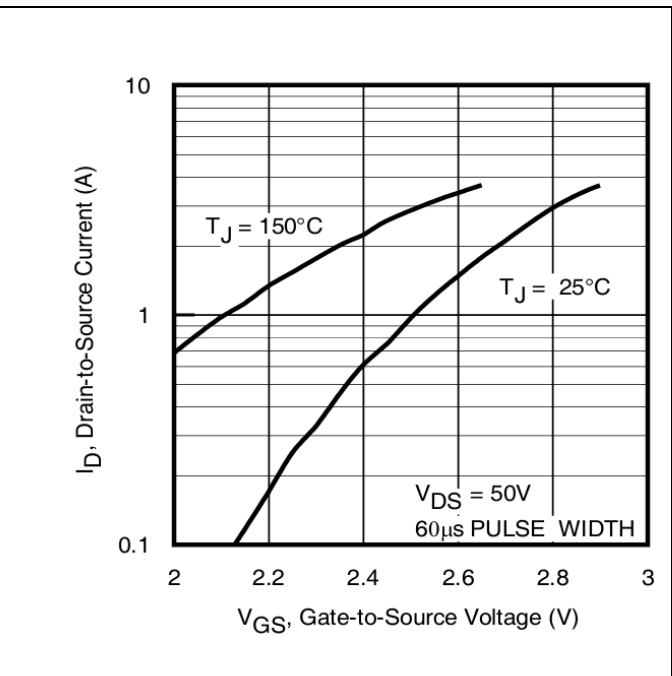


Figure 4 Typical Transfer Characteristics

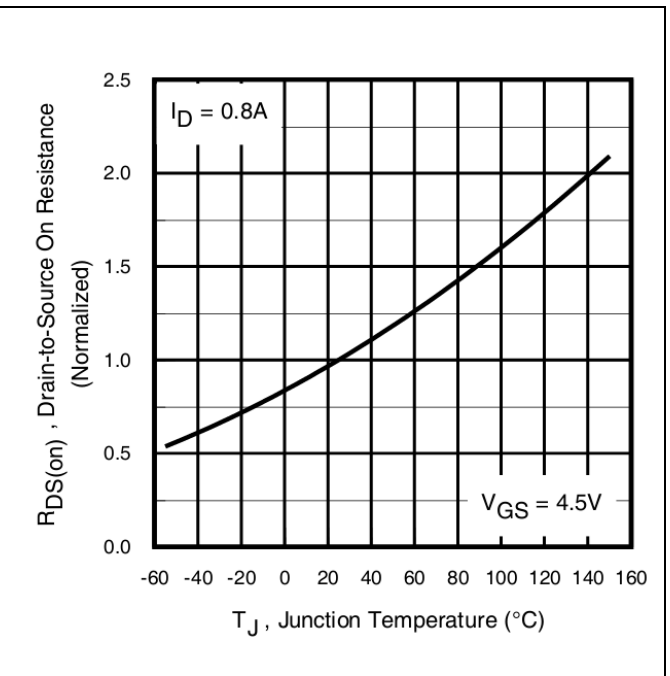


Figure 5 Normalized On-Resistance Vs. Temperature

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Radiation Hardened Logic Level Power MOSFET Thru-Hole (MO-036AB)

Electrical Characteristics Curves (Pre-irradiation)

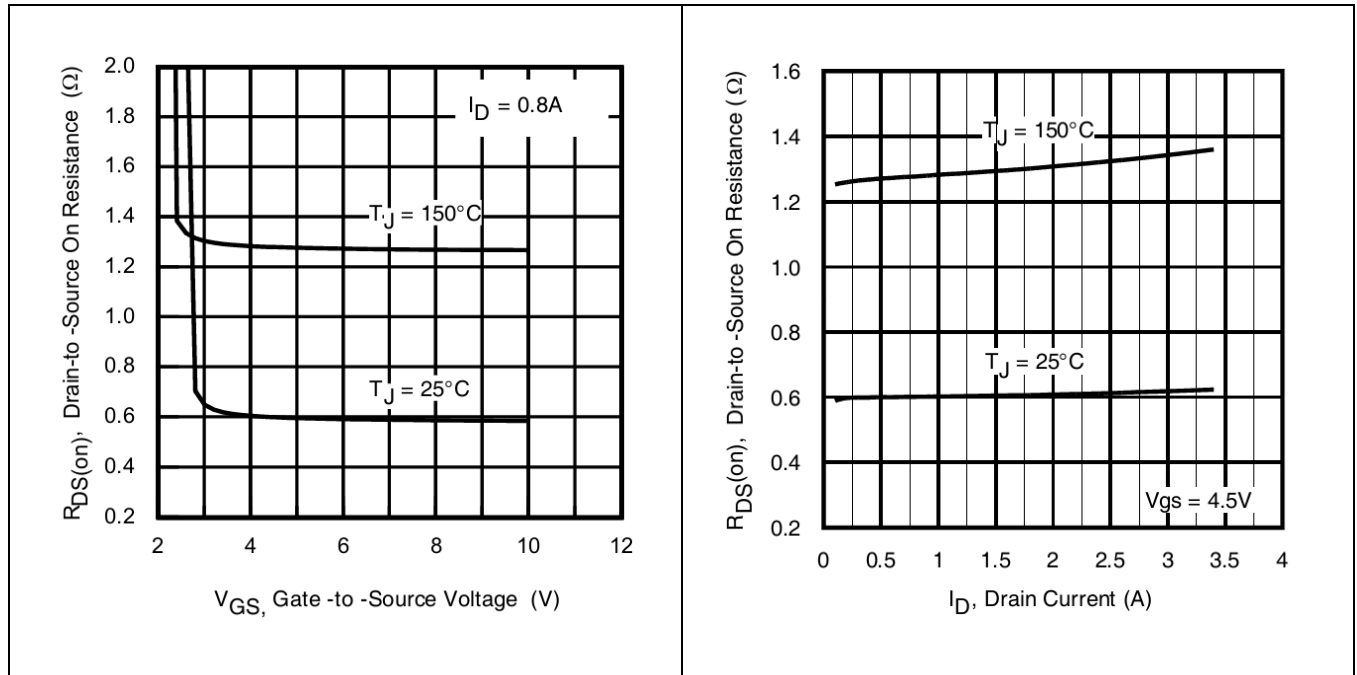


Figure 6 Typical On-Resistance Vs Gate Voltage

Figure 7 Typical On-Resistance Vs Drain Current

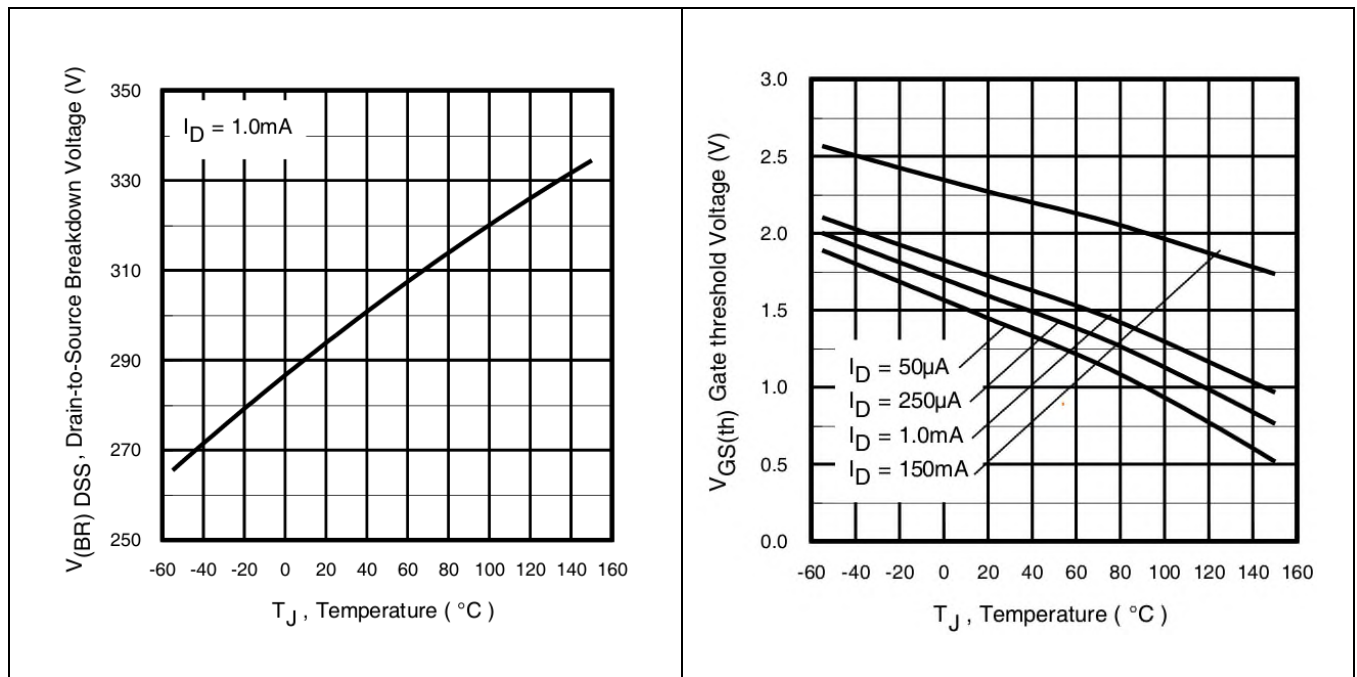


Figure 8 Typical Drain-to Source Breakdown Voltage Vs. Temperature

Figure 9 Typical Threshold Voltage Vs Temperature

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Radiation Hardened Logic Level Power MOSFET Thru-Hole (MO-036AB)

Electrical Characteristics Curves (Pre-irradiation)

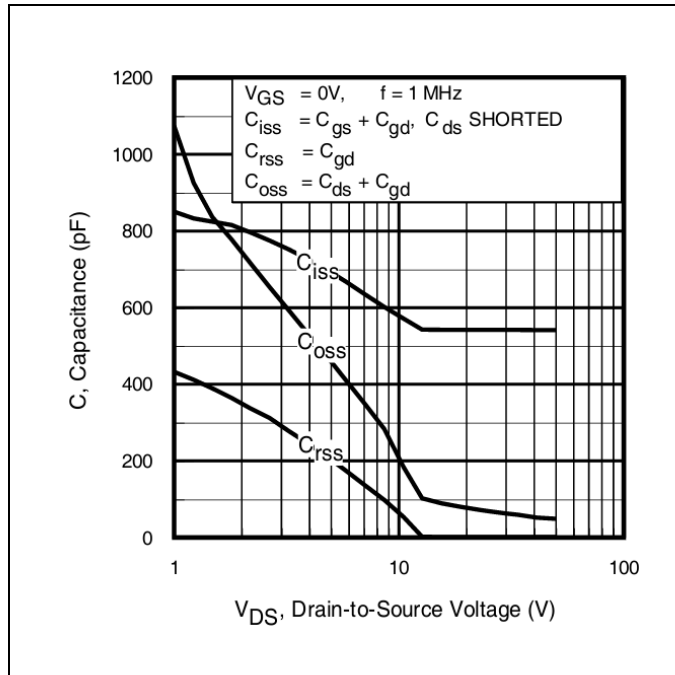


Figure 10 Typical Capacitance Vs. Drain-to-Source Voltage

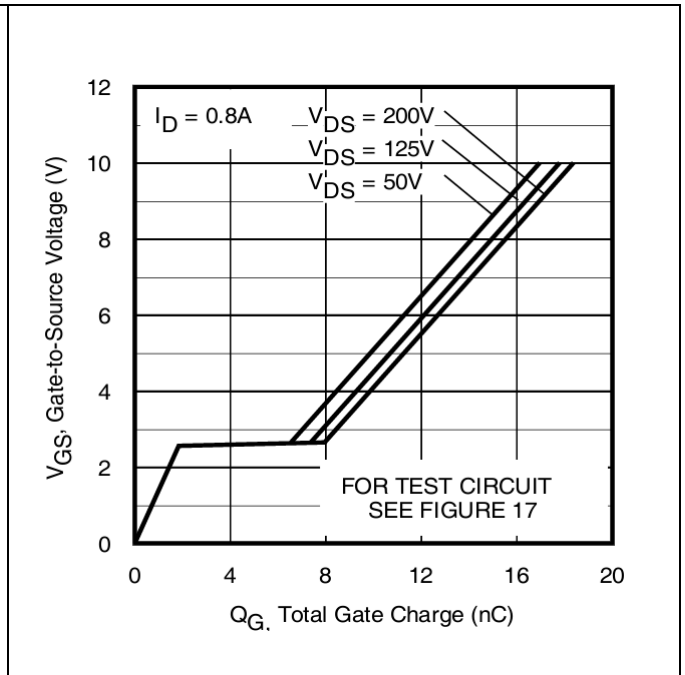


Figure 11 Typical Gate Charge Vs. Gate-to-Source Voltage

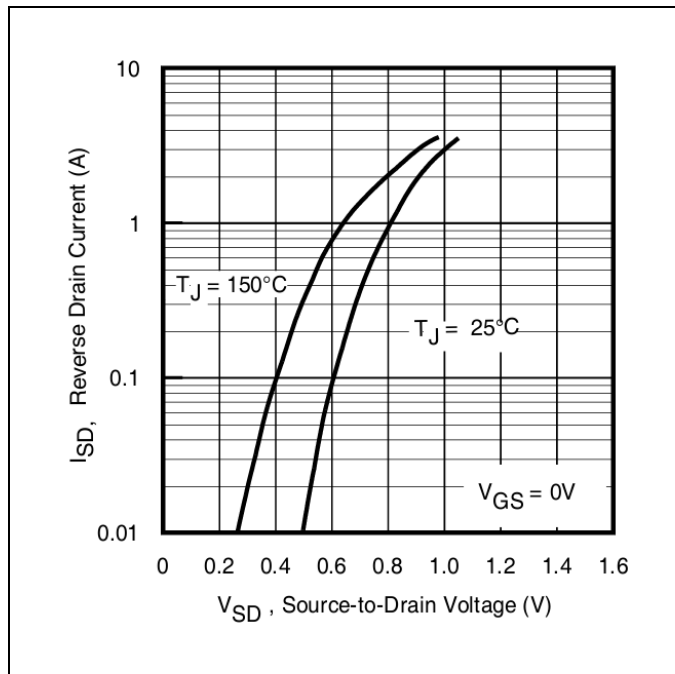


Figure 12 Typical Source-Drain Diode Forward Voltage

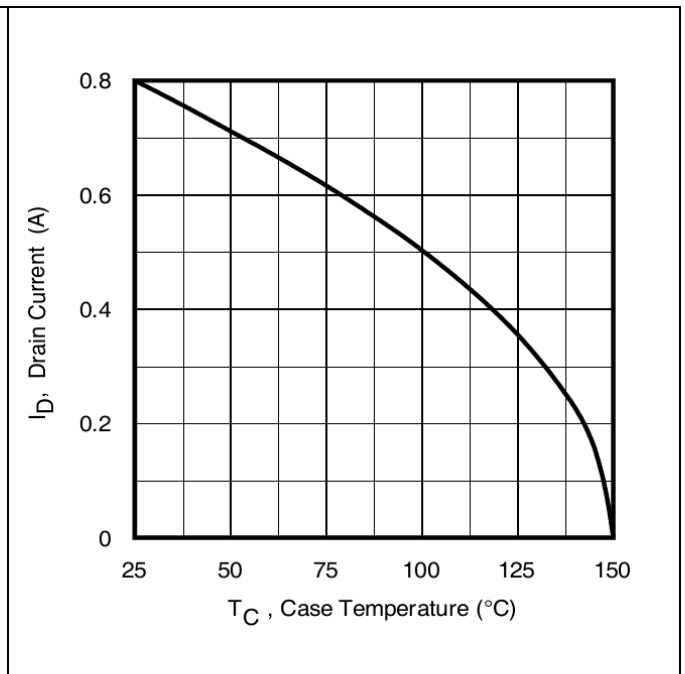
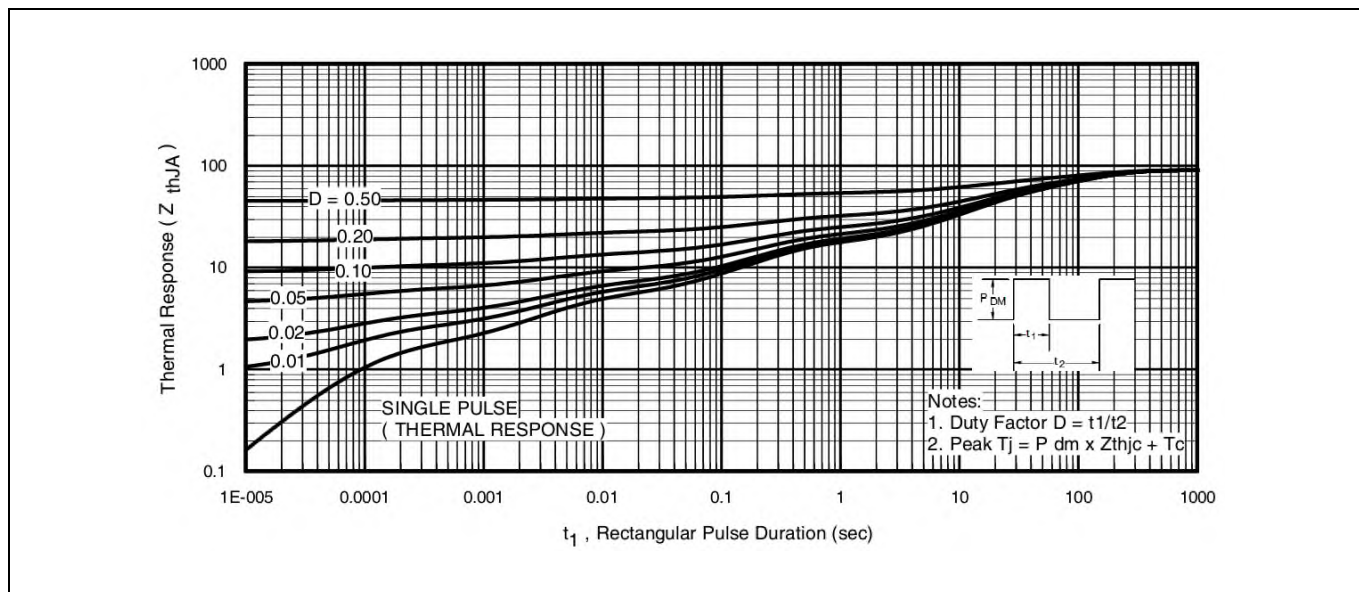
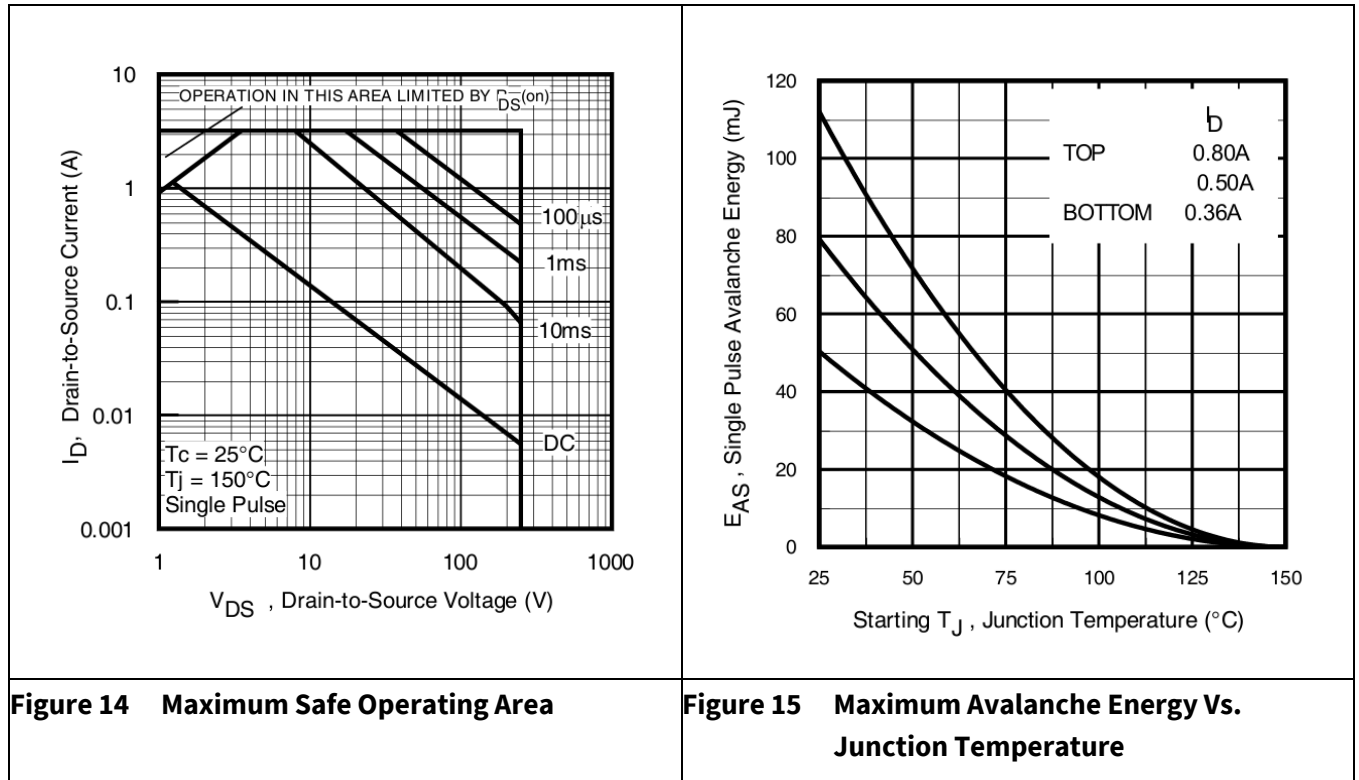


Figure 13 Maximum Drain Current Vs. Case Temperature

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Radiation Hardened Logic Level Power MOSFET Thru-Hole (MO-036AB)

Electrical Characteristics Curves (Pre-irradiation)



IRHLG7S7214 (2N7614M1)

Radiation Hardened Logic Level Power MOSFET Thru-Hole (MO-036AB)

Test Circuits (Pre-irradiation)

4 Test Circuits (Pre-irradiation)

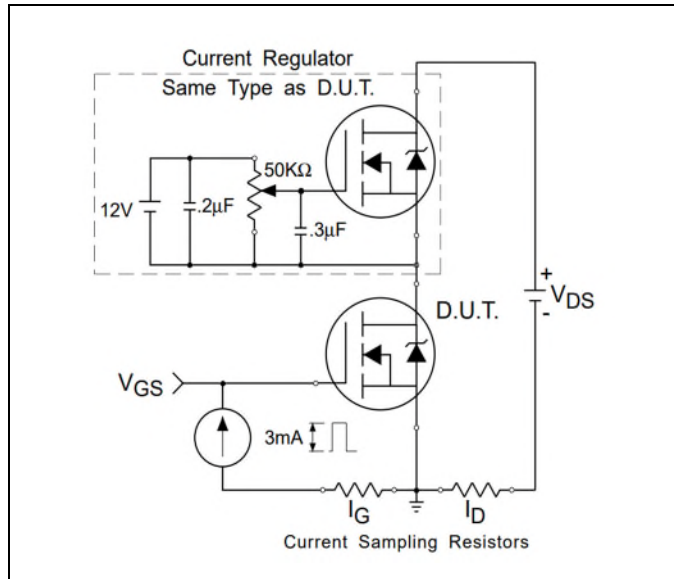


Figure 17 Gate Charge Test Circuit

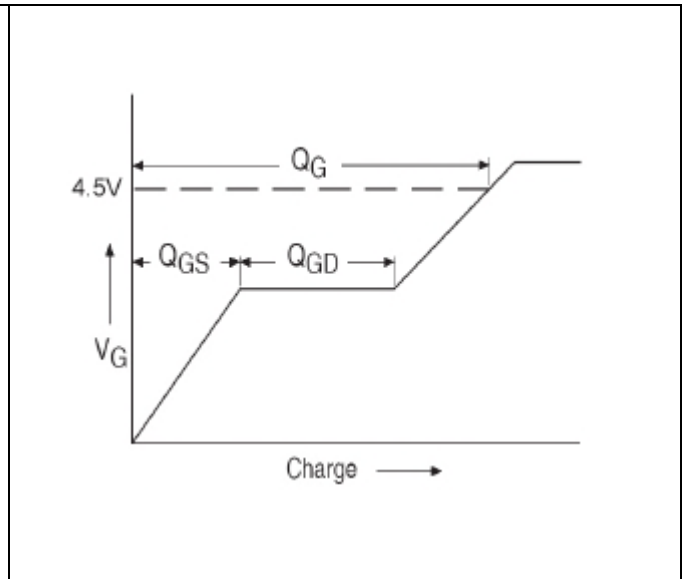


Figure 18 Gate Charge Waveform

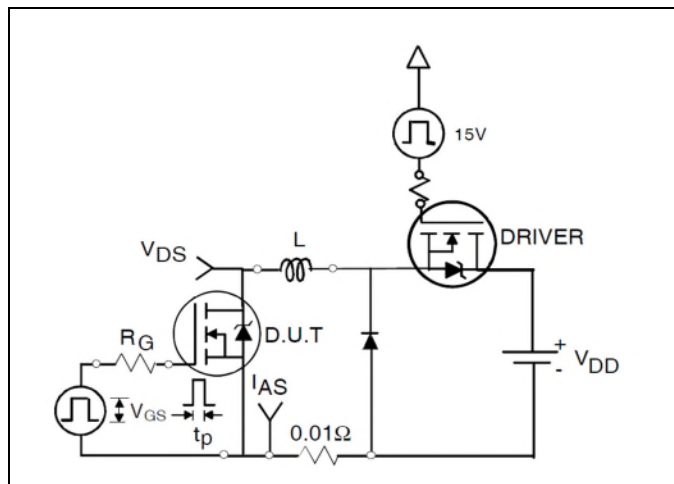


Figure 19 Unclamped Inductive Test Circuit

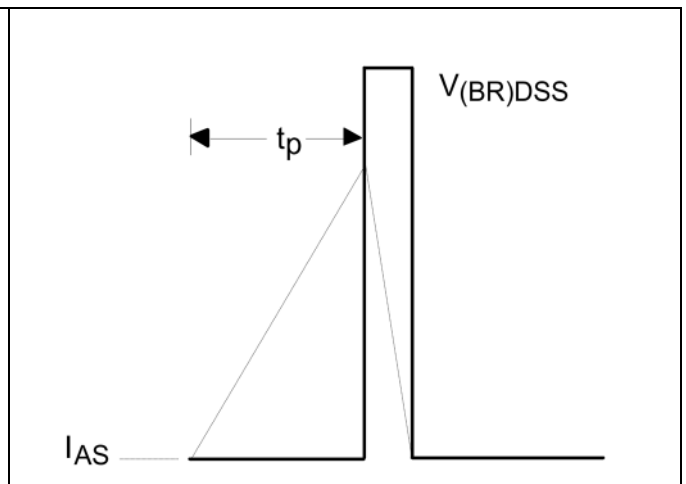


Figure 20 Unclamped Inductive Waveform

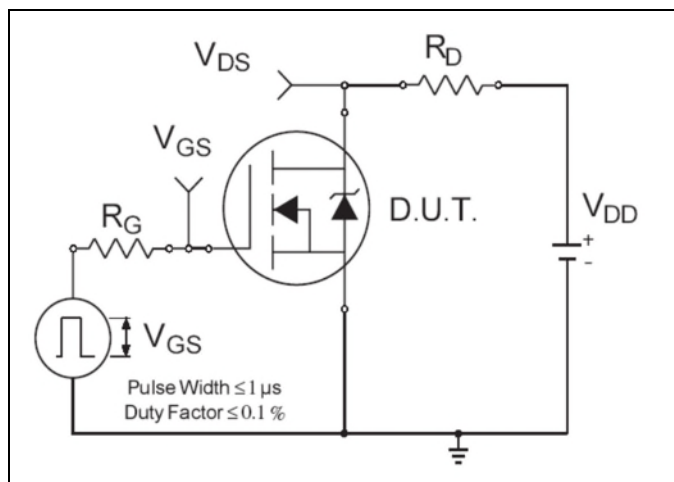


Figure 21 Switching Time Test Circuit

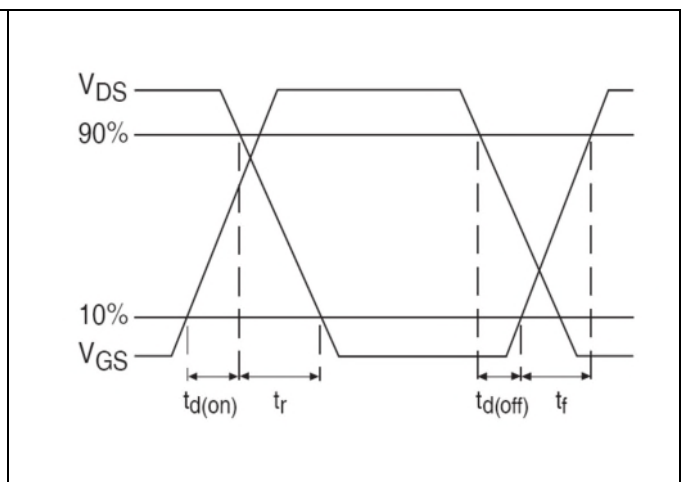


Figure 22 Switching Time Waveforms

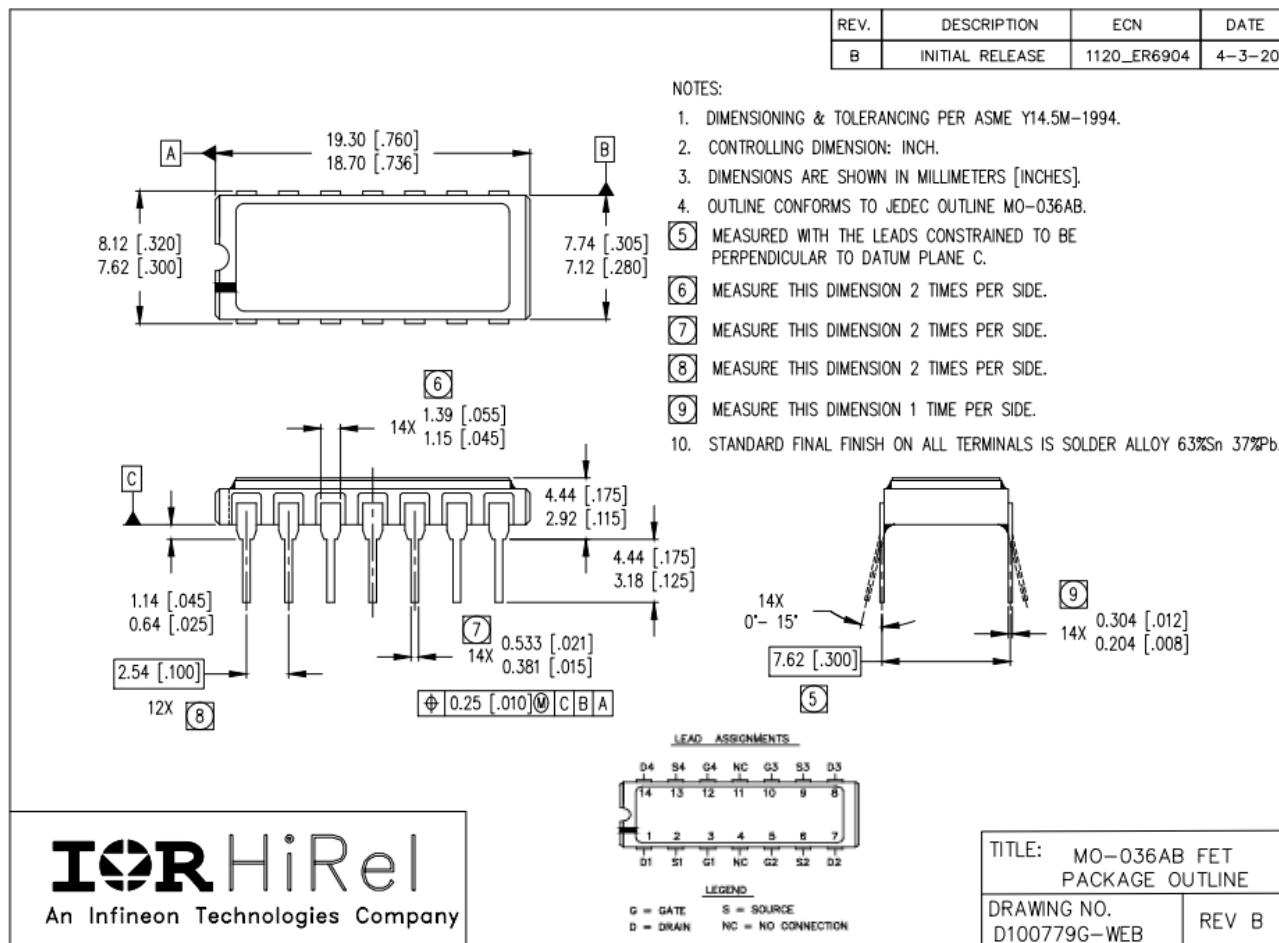
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Radiation Hardened Logic Level Power MOSFET Thru-Hole (MO-036AB)

Package Outline

5 Package Outline

Note: For the most updated package outline, please see the website: [MO-036AB](#)



Revision history**Revision history**

Document version	Date of release	Description of changes
	02/24/2016	Datasheet (PD-97832)
Rev A	02/25/2019	Updated based on ECN-1120_06644
Rev B	10/16/2020	Updated based on ECN-1120_08221
Rev C	04/27/2021	Updated based on ECN-1120_08546
Rev D	01/06/2023	Updated based on ECN-1120_09176

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